

FEATURES

- High Output Power: P5dB=50.0dBm (Typ.)
- High Gain: GL=12.0dB (Typ.)
- High P.A.E.: η_{add} =42% (Typ.)
- Broad Band: 7.7 to 8.5GHz
- Impedance Matched Zin/Zout = 50ohm
- Hermetically Sealed Package

DESCRIPTION

The SGK7785-100A is a high power GaN-HEMT that is internally matched for standard communication bands to provide optimum power and gain in a 50ohm system.



ABSOLUTE MAXIMUM RATING (Case Temperature Tc=25 deg.C)

Item	Symbol	Rating	Unit
Drain-Source Voltage	V _{DS}	26	V
Gate-Source Voltage	V _{GS}	-10	V
Total Power Dissipation	P _T	300	W
Storage Temperature	T _{stg}	-55 to +125	deg.C
Channel Temperature	T _{ch}	+250	deg.C

RECOMMENDED OPERATING CONDITION

Item	Symbol	Condition	Limit	Unit
Drain-Source Voltage	V _{DS}		≤24	V
Forward Gate Current	I _{GF}	R _g =25ohm	≤24.4	mA
Reverse Gate Current	I _{GR}	R _g =25ohm	≥-12.8	mA
Channel Temperature	T _{ch}		<+192	deg.C

ELECTRICAL CHARACTERISTICS (Case Temperature Tc=25 deg.C)

Item	Symbol	Condition	Limit			Unit
			Min.	Typ.	Max.	
Saturated Drain Current	I _{DSS}	V _{ds} =10V, V _{gs} =0V	-	26	-	A
Trans Conductance	G _m	V _{ds} =24V, V _{gs} =5.3A	-	12	-	S
Pinch-off Voltage	V _P	V _{ds} =24V, V _{gs} =5.3mA	-	-3	-	V
Output Power at 5dB G.C.P.	P5dB	V _{DS} =24V(Typ.) I _{DSDC} =4.0A(Typ.) f=7.7 to 8.5 GHz	49.0	50.0	-	dBm
Linear Gain at Pin=28.0dBm	GL		11.0	12.0	-	dB
Drain Current at 5dB G.C.P.	I _{dsr}		-	10	14	A
Power Added Efficiency at 3dB G.C.P.	η_{add}		-	42	-	%
Gain Flatness	ΔG		-	-	1.2	dB
3 rd Order Inter modulation Distortion	IM ₃	f=7.7GHz, 8.5GHz Δf =10MHz, 2-tone Test P _{out} =44.0dBm (S.C.L.)	-25.0	-	-	dBc
Thermal Resistance	R _{th}	Channel to Case	-	0.55	0.75	deg.C/W
Channel Temperature Rise	ΔT_{ch}	$(V_{DS} \times I_{dsr} - P_{out} + P_{in}) \times R_{th}$	-	88	140	deg.C

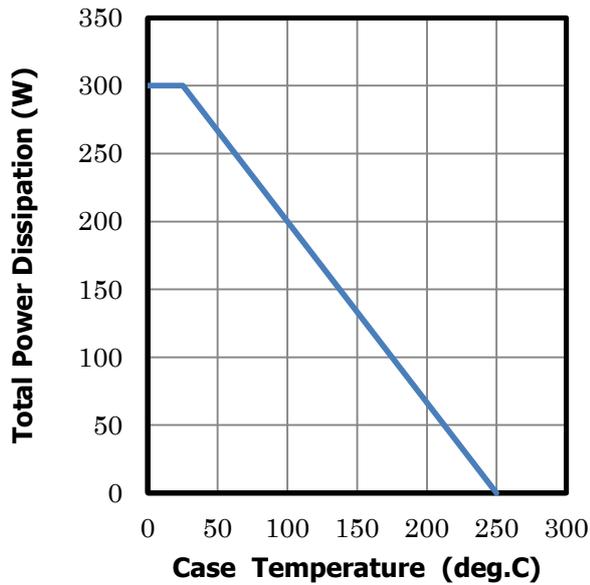
G.C.P. : Gain Compression Point, S.C.L. : Single Carrier Level

CASE STYLE	I2F
RoHS Compliance	YES
ESD	Class 1C 1000V to <2000V

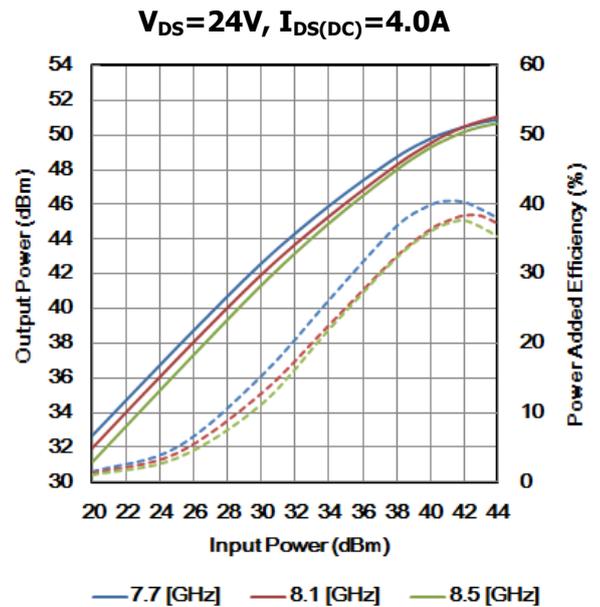
Note : Based on ANSI/ESDA/JEDEC JS-001-2012(C=100pF, R=1.5kohm)

- RF Characteristics

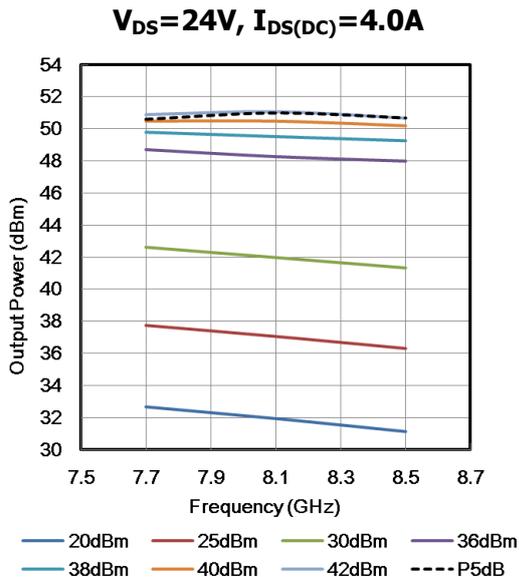
Power Derating Curve



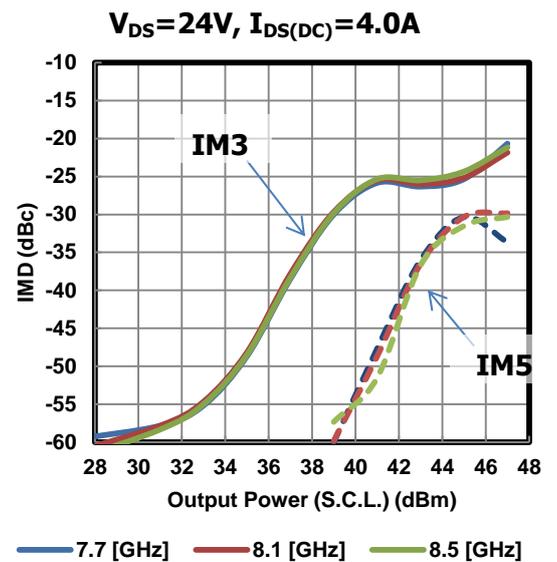
Output Power & Power Added Efficiency vs. Input Power



Output Power vs. Frequency



IMD vs. Output Power(S.C.L.)

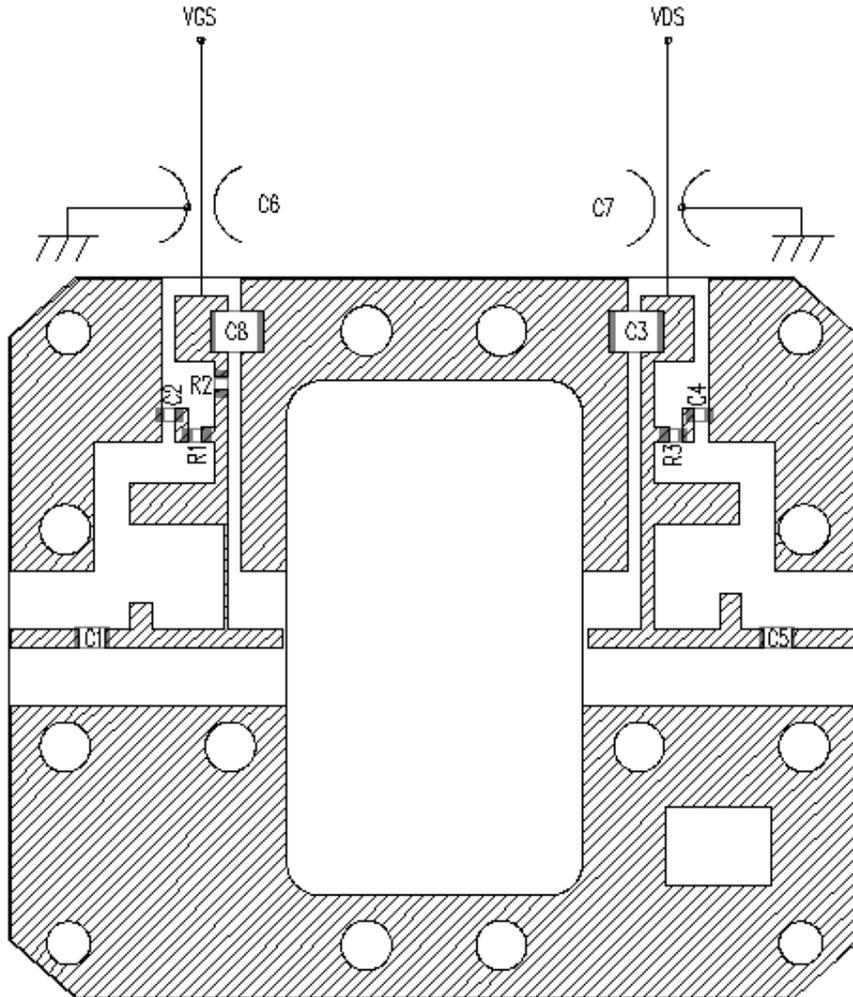


- S-parameter

Freq.	S11		S21		S12		S22	
	MAG	ANG	MAG	ANG	MAG	ANG	MAG	ANG
7500 MHz	0.731	17.2	2.878	160.4	0.057	96.6	0.302	16.0
7600 MHz	0.706	5.7	2.969	145.0	0.060	80.8	0.297	-1.7
7700 MHz	0.681	-2.2	3.035	133.3	0.063	69.1	0.291	-13.7
7800 MHz	0.650	-9.9	3.130	121.9	0.065	56.6	0.282	-26.3
7900 MHz	0.600	-19.9	3.281	105.8	0.069	40.1	0.252	-42.0
8000 MHz	0.551	-26.8	3.457	93.8	0.073	27.0	0.219	-55.8
8100 MHz	0.485	-34.0	3.622	80.0	0.076	14.3	0.169	-76.3
8200 MHz	0.366	-44.3	3.904	59.9	0.084	-4.6	0.099	-144.1
8300 MHz	0.240	-45.3	4.014	42.9	0.088	-21.3	0.139	150.1
8400 MHz	0.144	-15.3	3.961	25.3	0.089	-38.5	0.244	115.4
8500 MHz	0.218	25.0	3.711	3.0	0.087	-59.7	0.391	86.8
8600 MHz	0.321	28.3	3.491	-11.8	0.084	-75.0	0.475	68.6
8700 MHz	0.406	22.9	3.225	-26.2	0.080	-88.7	0.538	54.8

● Amplifier Circuit Outline

SGK7785-100A



C1	2.0pF
C2	1000pF
C3	0.1uF
C4	1000pF
C5	2.0pF
C6	1000pF
C7	1000pF
C8	0.1uF
R1	51Ω
R2	25Ω
R3	51Ω

Rogers RO4003C

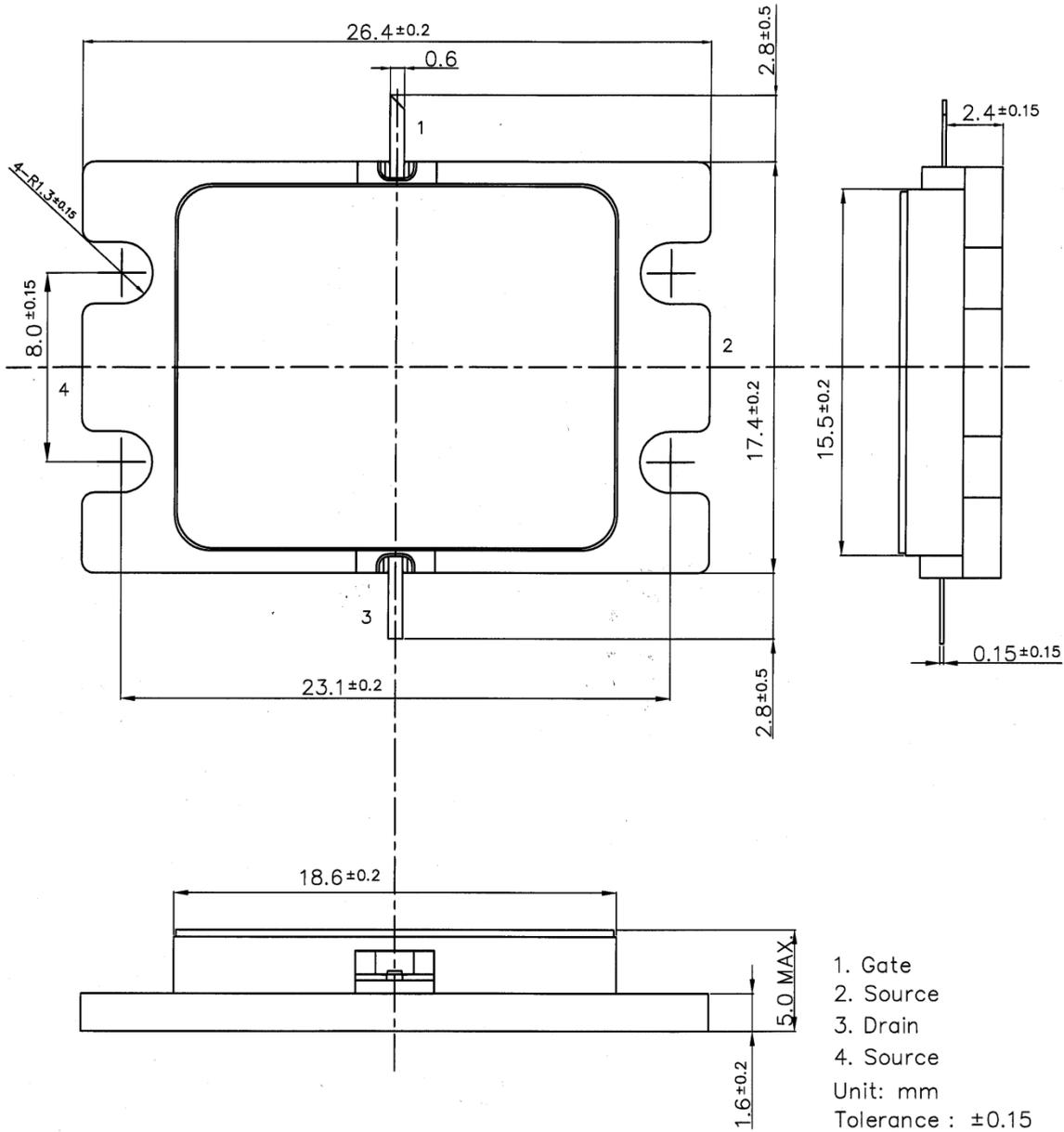
$h=0.542\text{mm}$ $\epsilon_r=3.38$

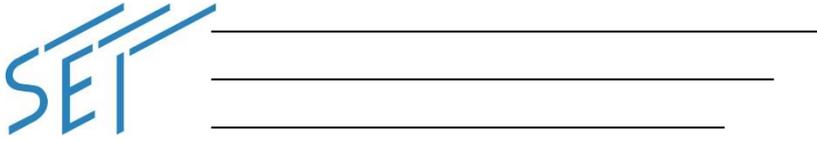
$Cu=18\mu\text{m}$ Unit:mm

C1, C5 : ATC 600F(0805), $\pm 0.1\text{pF}$

C6, C7 : EMI FILTER MARUWA (FTA352AR102S-S)

● **Package Out Line**
Case Style: I2F





SGK7785-100A
C-Band Internally Matched GaN-HEMT

For further information please contact:

<http://global-sei.com/Electro-optic/about/office.html>